

Please amend the present application as follows:

Claims

The following is a copy of Applicant's claims that identifies language being added with underlining ("___") and language being deleted with strikethrough ("—"), as is applicable:

1. (Previously presented) A system comprising:
a high-density non-volatile fast memory having no erasing circuitry; and
an ultraviolet (UV) light window adapted to expose the high-density non-volatile fast memory to UV light.
2. (Original) The system of claim 1, wherein the high-density non-volatile fast memory comprises a modified flash memory having no erasing circuitry.
3. (Original) The system of claim 1, wherein the high-density non-volatile fast memory comprises a two-terminal drain-gate-connected modified flash cell having no erasing circuitry.
4. (Original) The system of claim 3, wherein the two-terminal drain-gate-connected modified flash cell is a diode-connected nitrided read-only memory (NROM) cell.

5. (Original) A device comprising:
two-terminal drain-gate-connected modified flash cells having no erasing circuitry; and
an ultraviolet (UV) light window adapted to expose the two-terminal drain-gate-connected modified flash cells to UV light.

6. (Original) The device of claim 5, wherein the two-terminal drain-gate-connected modified flash cells are configured as a two-dimensional planar matrix of cells.

7. (Original) The device of claim 6, wherein the two-dimensional planar matrix of cells is a NAND configuration.

8. (Original) The device of claim 6, wherein the two-dimensional planar matrix of cells is a NOR configuration.

9. (Original) The device of claim 5, wherein the two-terminal drain-gate-connected modified flash cells are configured as three-dimensional layers.

10. (Original) A system comprising:
modified flash cells having no erasing circuitry; and
an ultraviolet (UV) light window adapted to expose the modified flash cells to UV light.

11. (Original) The system of claim 10, wherein the UV light window is located above a control gate of the modified flash cells.

12. (Original) The system of claim 10, wherein the UV light window is located below a substrate of the modified flash cells.

13. (Original) The system of claim 10, wherein the UV light window is interposed between control gates of the modified flash cells.

14. (Original) The system of claim 10, wherein the UV light window is offset from control gates of the modified flash cells.

15. (Original) The system of claim 10, wherein the UV light window is adapted to diffuse UV light entering the UV light window.

16. (Original) The system of claim 10, wherein the modified flash cells are arranged in a NAND configuration.

17. (Original) The system of claim 10, wherein the modified flash cells are arranged in a NOR configuration.

18. (Original) The system of claim 10, wherein the modified flash cells are configured as a two-dimensional planar matrix of cells.

19. (Original) The system of claim 18, wherein the two-dimensional planar matrix of cells is a NAND configuration.

20. (Original) The system of claim 18, wherein the two-dimensional planar matrix of cells is a NOR configuration.

21. (Original) The system of claim 10, wherein the modified flash cells are configured as three-dimensional layers.

22. (Original) The system of claim 21, wherein the three-dimensional layers comprise modified flash cells arranged in a NAND configuration.

23. (Original) The system of claim 21, wherein the three-dimensional layers comprise modified flash cells arranged in a NOR configuration.

24. (Original) The system of claim 10, further comprising an electronic device adapted to house the modified flash cells, the electronic device having an opening to receive the UV light window.

25. (Original) The system of claim 24, wherein the electronic device is a portable electronic device.

26. (Original) The system of claim 25, wherein the portable electronic device is a cellular telephone.

27. (Original) The system of claim 25, wherein the portable electronic device is a personal digital assistant (PDA).

28. (Original) The system of claim 25, wherein the portable electronic device is an MP3 player.

29. (Original) The system of claim 25, wherein the portable electronic device is a lap-top computer.

30. (Previously presented) A method comprising:
exposing a high-density non-volatile fast memory to ultraviolet (UV) light; and
erasing the high-density non-volatile fast memory using the UV light without
the use of any erasing circuitry.

31. (Original) The method of claim 30 further comprising:
passing light through a UV light window.

32. (Previously presented) A method comprising:
exposing a modified flash cell to ultraviolet (UV) light; and
erasing the modified flash cell using the UV light without the use of any
erasing circuitry.

33. (Previously presented) A method comprising:
installing ultraviolet (UV) windows onto portable electronic devices having non-volatile memory;
passing UV light through the UV windows; and
erasing the non-volatile memory by exposing the non-volatile memory to the UV light through the UV light windows without the use of any erasing circuitry.

34. (Original) A system comprising:
means for exposing a modified flash cell to ultraviolet (UV) light; and
means for erasing the modified flash cell using the UV light without the use of any erasing circuitry.

35. (Previously presented) A system comprising:
means for installing ultraviolet (UV) windows onto portable electronic devices having non-volatile memory; and
means for erasing the non-volatile memory by exposing the non-volatile memory to UV light through the UV light windows without the use of any erasing circuitry.

36. (Previously presented) A device comprising:
two-terminal drain-gate-connected modified flash cells; and
an ultraviolet (UV) light window adapted to expose the two-terminal drain-gate-connected modified flash cells to UV light.

37. (Previously presented) The device of claim 36, wherein the two-terminal drain-gate-connected modified flash cells are configured as a two-dimensional planar matrix of cells.

38. (Previously presented) The device of claim 37, wherein the two-dimensional planar matrix of cells is a NAND configuration.

39. (Previously presented) The device of claim 37, wherein the two-dimensional planar matrix of cells is a NOR configuration.

40. (Previously presented) The device of claim 36, wherein the two-terminal drain-gate-connected modified flash cells are configured as three-dimensional layers.

41. (Previously presented) A system comprising:
a non-volatile memory; and
an ultraviolet (UV) light window adapted to expose the high-density non-volatile fast memory to UV light, wherein the UV light window is located below a substrate of the memory.

42. (Previously presented) The system of claim 41, wherein the UV light window is adapted to diffuse UV light entering the UV light window.

43. (Previously presented) A system comprising:

a non-volatile memory; and

an ultraviolet (UV) light window adapted to expose the high-density non-volatile fast memory to UV light, wherein the UV light window is located below a substrate of the memory, wherein the UV light window is interposed between control gates of the modified flash cells.

44. (Previously presented) The system of claim 43, wherein the UV light window is adapted to diffuse UV light entering the UV light window.